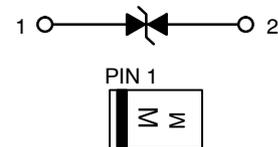
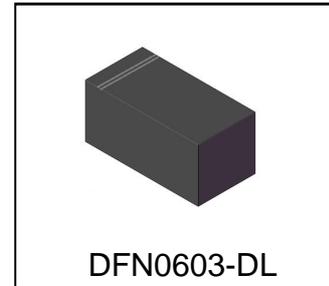


LESD11D12CT5G ESD PROTECTION DIODE

Discription

The LESD11D12CT5G is designed to protect voltage sensitive components from ESD. Excellent clamping capability, low leakage, and fast response time provide best in class protection on designs that are exposed to ESD. Because of its small size, it is suited for use in cellular phones, digital cameras and many other portable applications where board space is at a premium.

LESD11D12CT5G



M = Specific Device Code
M = Month Code

Applications

- | Cellular phones audio
- | Digital cameras
- | Portable applications
- | Mobile telephone

Features

- | Small Body Outline Dimensions:
0.61 mm x 0.31 mm
- | Low Body Height: " 0.28 mm
- | Low Leakage
- | Response Time is Typically < 1 ns
- | ESD Rating of Class 3 per Human Body Model
- | IEC61000-4-2 Level 4 ESD Protection
- | We declare that the material of product compliance with RoHS requirements and Halogen Free.

Ordering information

Device	Marking	Shipping
LESD11D12CT5G	M (Rotate 90°cw)	15000/Tape&Reel

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
IEC 61000-4-2 (ESD) Air Contact Contact discharge		±25 ±20	kV kV
Total Power Dissipation on FR-5 Board (Note 1) @ T _A =25°C	PD	200	mW
Junction and Storage Temperature Range	T _J ,T _{STG}	-55 to 150	°C
Lead Solder Temperature – Maximum (10 Second Duration)	TL	260	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Rating are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

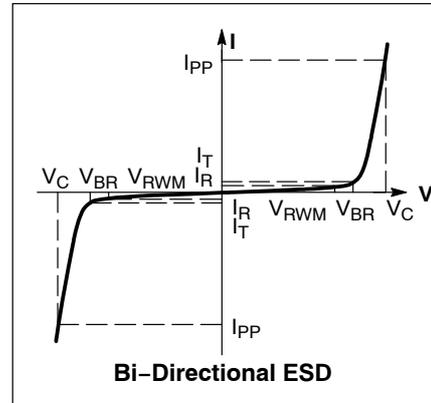
1. FR-5 = 1.0*0.75*0.62 in.

LESD11D12CT5G

ELECTRICAL CHARACTERISTICS

(T_A = 25°C unless otherwise noted)

Symbol	Parameter
I _{PP}	Maximum Reverse Peak Pulse Current
V _C	Clamping Voltage @ I _{PP}
V _{RWM}	Working Peak Reverse Voltage
I _R	Maximum Reverse Leakage Current @ V _{RWM}
V _{BR}	Breakdown Voltage @ I _T
I _T	Test Current
P _{pk}	Peak Power Dissipation
C	Capacitance @ V _R = 0 and f = 1.0 MHz



ELECTRICAL CHARACTERISTICS

Device	V _{RWM} (V)	I _R (μA) @ V _{RWM}	V _{BR} (V) @ I _T (Note 1)		I _T (mA)	I _{PP} (A)	V _C (V) @ Max I _{PP}	P _{PK} (W) (8*20 μs)	C (pF)		
	Max	Max	Min	Max		Max	Max	Max	Min	Typ	Max
LESD11D12CT5G	12	1.0	13.3	16	1.0	4	24	95	3.5	6.5	9.5

- V_{BR} is measured with a pulse test current I_T at an ambient temperature of 25°C
- Surge current waveform per Figure 3.

LESD11D12CT5G

TYPICAL CHARACTERISTICS



Figure 1. Positive 8kV contact per IEC 61000-4-2-LESD11D12CT5G



Fig 2. Negative 8kV contact per IEC 61000-4-2-LESD11D12CT5G

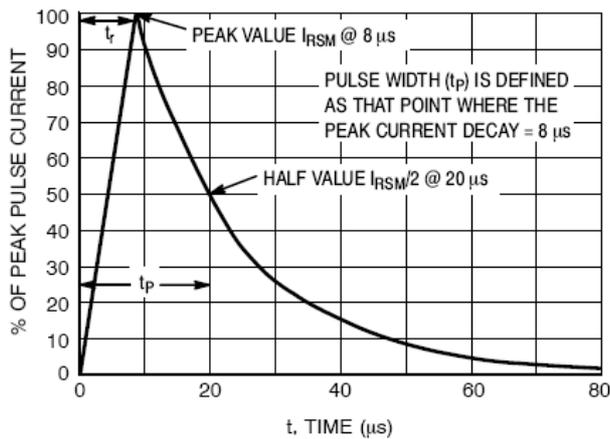
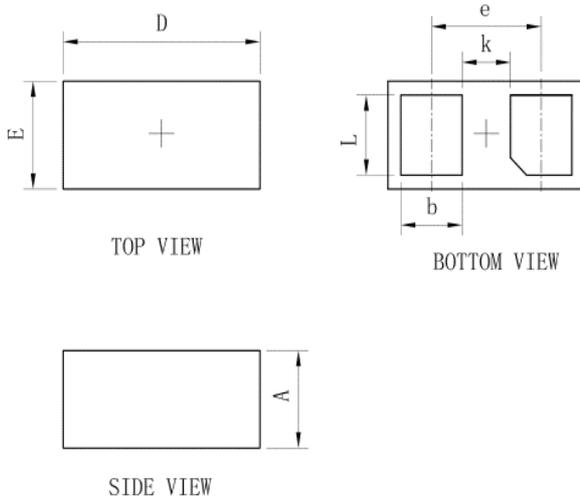


Figure 3. 8*20 μ s Pulse Waveform

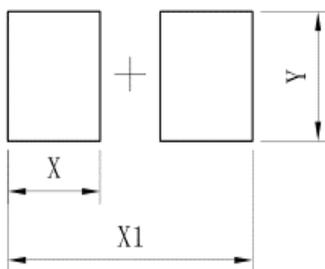
LESD11D12CT5G

OUTLINE AND DIMENSIONS



DFN0603-DL			
Dim	Min	Typ.	Max
D	0.58	0.61	0.64
E	0.28	0.31	0.34
e	-	0.34	-
L	0.20	0.23	0.26
b	0.16	0.19	0.22
A	0.25	0.28	0.31
k	0.12	0.15	0.18
All Dimensions in mm			

SOLDERING FOOTPRINT



DFN0603-DL	
DIM	(mm)
X	0.23
X1	0.61
Y	0.30

DISCLAIMER

- Before you use our Products, you are requested to carefully read this document and fully understand its contents. LRC shall not be in any way responsible or liable for failure, malfunction or accident arising from the use of any LRC's Products against warning, caution or note contained in this document.
- All information contained in this document is current as of the issuing date and subject to change without any prior notice. Before purchasing or using LRC's Products, please confirm the latest information with a LRC sales representative.